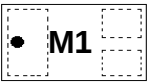
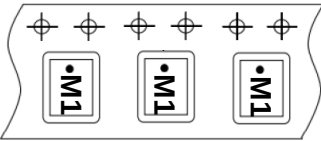
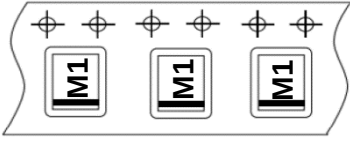
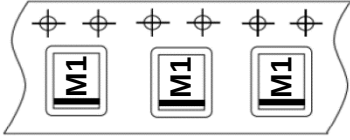


Marking Information

DMN26D0UFB4-7	 Top View Dot Denotes Drain Side From date code 1527 (YYWW), this changes to:  Top View Bar Denotes Gate and Source Side  
DMN26D0UFB4-7B	 Top View Bar Denotes Gate and Source Side  M1 = Part Marking Code

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain Source Voltage			V _{DSS}	20	V
Gate-Source Voltage			V _{GSS}	±10	V
Continuous Drain Current (Note 5) V _{GS} = 4.5V	Steady State	T _A = +25°C T _A = +70°C	I _D	240 190	mA
Continuous Drain Current (Note 5) V _{GS} = 1.8V	Steady State	T _A = +25°C T _A = +70°C	I _D	180 140	mA
Pulsed Drain Current - t _P = 10μs			I _{DM}	805	mA

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 5) @T _A = +25°C	P _D	350	mW
Thermal Resistance, Junction to Ambient (Note 5)	R _{θJA}	357	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

Note: 5. Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 6)						
Drain-Source Breakdown Voltage	BV _{DSS}	20	—	—	V	V _{GS} = 0V, I _D = 100μA
Zero Gate Voltage Drain Current @ T _C = +25°C	I _{DSS}	—	—	500	nA	V _{DS} = 20V, V _{GS} = 0V
Gate-Body Leakage	I _{GSS}	—	—	±1 ±100	μA nA	V _{GS} = ±10V, V _{DS} = 0V V _{GS} = ±5V, V _{DS} = 0V
ON CHARACTERISTICS (Note 6)						
Gate Threshold Voltage	V _{GS(TH)}	0.6	—	0.9	V	V _{DS} = V _{GS} , I _D = 250μA
Static Drain-Source On-Resistance	R _{DS(ON)}	— — — —	1.8 2.5 3.4 4.7	3.0 4.0 6.0 10.0	Ω	V _{GS} = 4.5V, I _D = 100mA V _{GS} = 2.5V, I _D = 50mA V _{GS} = 1.8V, I _D = 20mA V _{GS} = 1.5V, I _D = 10mA
Forward Transconductance	Y _{fs}	180	242	—	mS	V _{DS} = 10V, I _D = 0.1A
Source-Drain Diode Forward Voltage	V _{SD}	0.5	—	1.4	V	V _{GS} = 0V, I _S = 115mA
DYNAMIC CHARACTERISTICS (Note 7)						
Input Capacitance	C _{iss}	—	14.1	28.2	pF	V _{DS} = 15V, V _{GS} = 0V f = 1.0MHz
Output Capacitance	C _{oss}	—	2.9	5.8	pF	
Reverse Transfer Capacitance	C _{rss}	—	1.6	3.2	pF	
SWITCHING CHARACTERISTICS (Note 7)						
Turn-On Delay Time	t _{D(ON)}	—	3.8	—	ns	V _{GS} = 4.5V, V _{DD} = 10V I _D = 200mA, R _G = 2.0Ω
Rise Time	t _R	—	7.9	—		
Turn-Off Delay Time	t _{D(OFF)}	—	13.4	—		
Fall Time	t _F	—	15.2	—		

Notes: 6. Short duration pulse test used to minimize self-heating effect.
 7. Guaranteed by design. Not subject to product testing.

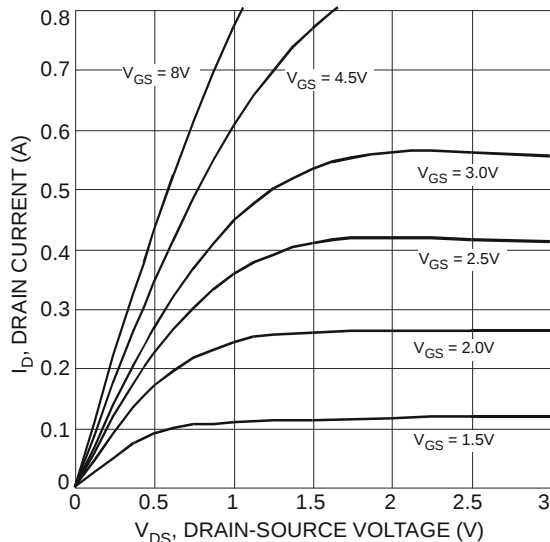


Fig. 1 Typical Output Characteristic

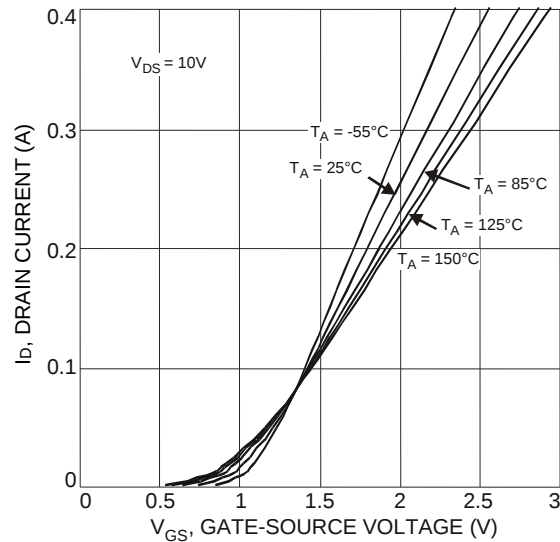


Fig. 2 Typical Transfer Characteristic

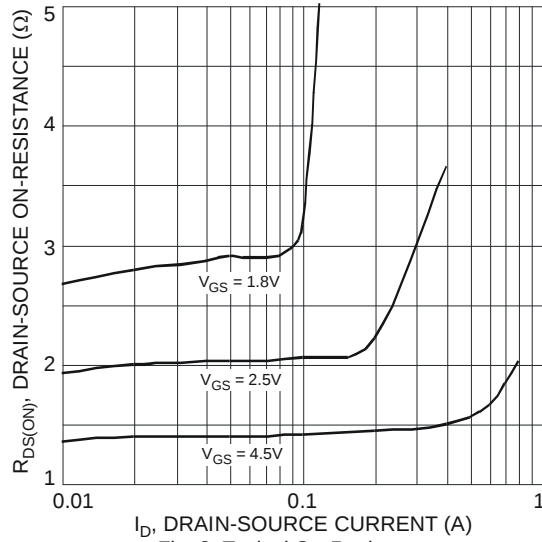


Fig. 3 Typical On-Resistance vs. Drain Current and Gate Voltage

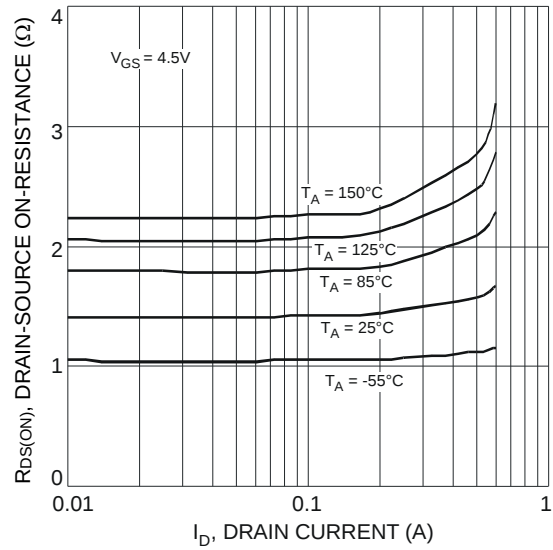


Fig. 4 Typical On-Resistance vs. Drain Current and Temperature

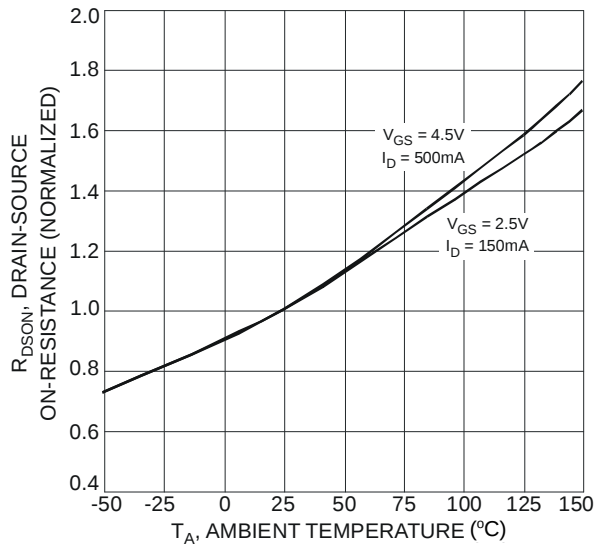


Fig. 5 On-Resistance Variation with Temperature

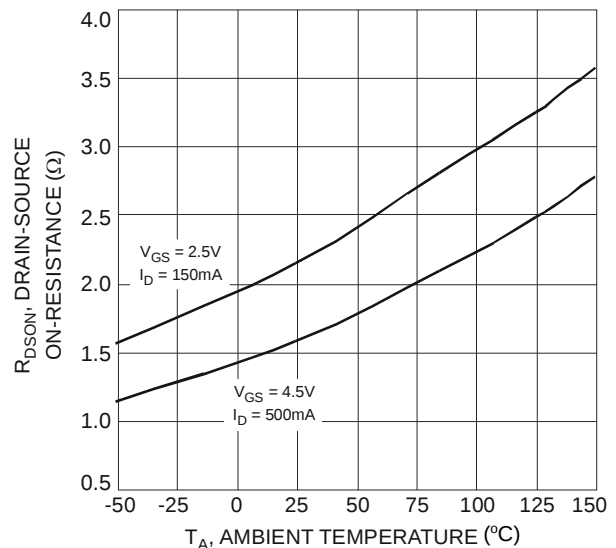


Fig. 6 On-Resistance Variation with Temperature

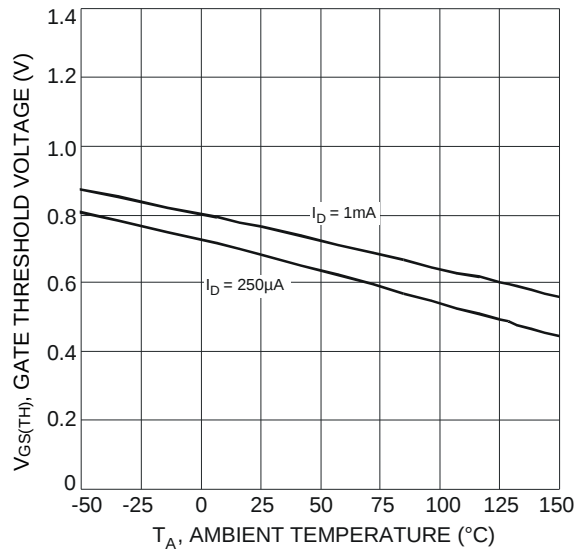


Fig. 7 Gate Threshold Variation vs. Ambient Temperature

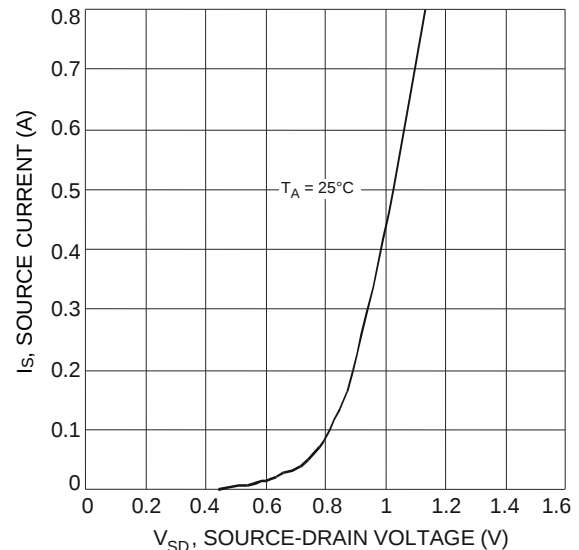


Fig. 8 Diode Forward Voltage vs. Current

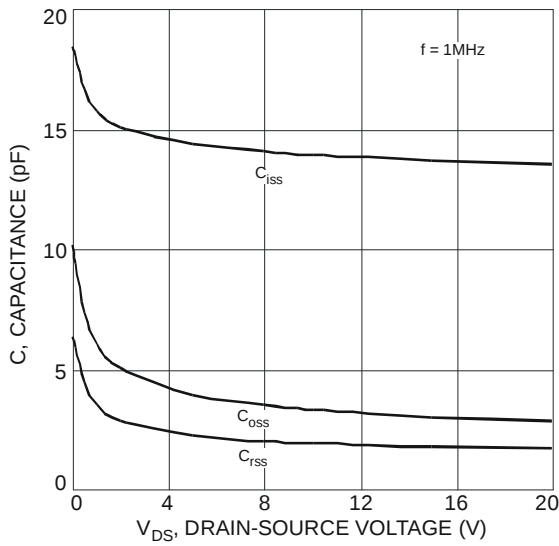


Fig. 9 Typical Total Capacitance

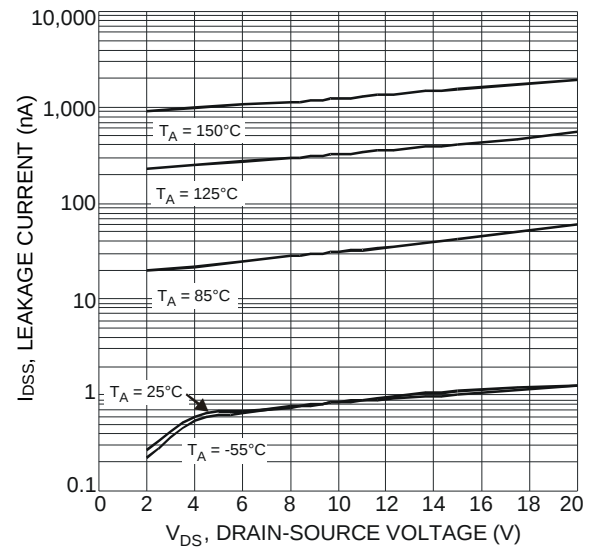


Fig. 10 Typical Leakage Current vs. Drain-Source Voltage

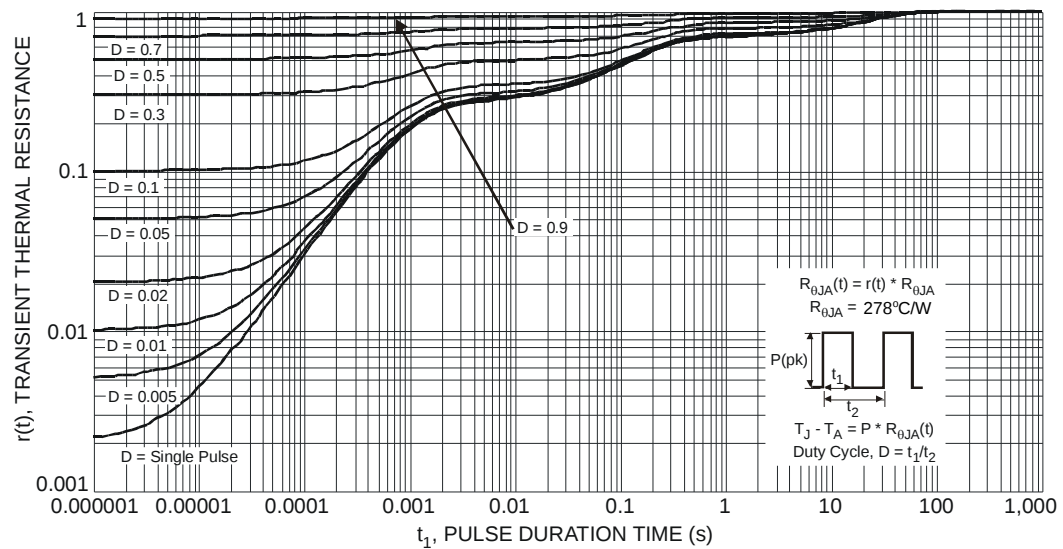
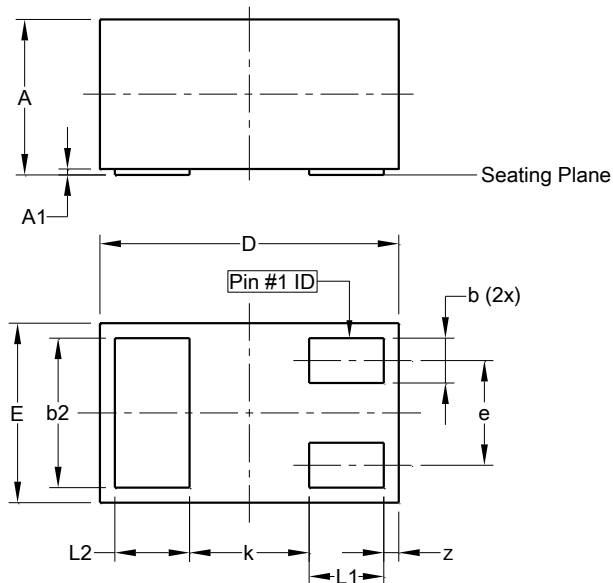


Fig. 11 Transient Thermal Response

Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

X2-DFN1006-3

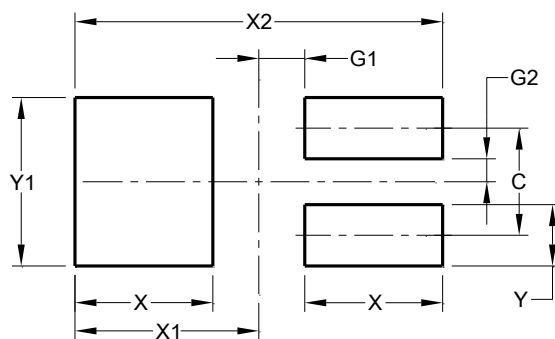


X2-DFN1006-3			
Dim	Min	Max	Typ
A	—	0.40	—
A1	0.00	0.05	0.03
b	0.10	0.20	0.15
b2	0.45	0.55	0.50
D	0.95	1.05	1.00
E	0.55	0.65	0.60
e	—	—	0.35
L1	0.20	0.30	0.25
L2	0.20	0.30	0.25
k	—	—	0.40
z	0.02	0.08	0.05
All Dimensions in mm			

Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

X2-DFN1006-3



Dimensions	Value (in mm)
C	0.350
G1	0.150
G2	0.075
X	0.450
X1	0.600
X2	1.200
Y	0.200
Y1	0.550

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